

2N6764, JANTX2N6764, JANTXV2N6764
2N6766, JANTX2N6766, JANTXV2N6766

2N6768, JANTX2N6768, JANTXV2N6768
2N6770, JANTX2N6770, JANTXV2N6770

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	JANTXV, JANTX, 2N6764	Units
I_D @ $V_{GS} = 10\text{V}$, $T_C = 25^\circ\text{C}$ Continuous Drain Current	38	A
I_D @ $V_{GS} = 10\text{V}$, $T_C = 100^\circ\text{C}$ Continuous Drain Current	24	A
I_{DM} Pulsed Drain Current ¹	152	A
P_D @ $T_C = 25^\circ\text{C}$ Maximum Power Dissipation	150	W
Linear Derating Factor	1.2	W/ $^\circ\text{C}$
V_{GS} Gate-Source Voltage	± 20	V
E_{AS} Single Pulse Avalanche Energy ²	150 ⁴	mJ
I_{AR} Avalanche Current ¹	38 ⁴	A
T_J Operating Junction	-55 to 150	$^\circ\text{C}$
T_{STG} Storage Temperature Range		$^\circ\text{C}$
Lead Temperature	300(.06 from case for 10 sec)	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS} Drain-Source Breakdown Voltage	100			V	$V_{GS} = 0\text{V}$, $I_D \approx 1.0\text{ mA}$
$R_{DS(on)}$ Static Drain-to-Source On-State Resistance	—	—	0.055		$V_{GS} = 10\text{V}$, $I_D = 24\text{ A}$ ³
	—	—	0.065		$V_{GS} = 10\text{V}$, $I_D = 38\text{ A}$ ³
$V_{GS(th)}$ Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$
I_{DSS} Zero Gate Voltage Drain Current	—	—	25	μA	$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{V}$
	—	—	250	μA	$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{V}$, $T_J = 125^\circ\text{C}$
I_{SSS} Gate -to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20\text{ V}$
I_{SSS} Gate -to-Source Leakage Reverse	—	—	-100	nA	$V_{GS} = -20\text{ V}$
$Q_{G(on)}$ On-state Gate Charge	50	—	125	nC	$V_{GS} = 10\text{V}$, $I_D = 38\text{A}$
Q_{GS} Gate-to-Source Charge	8	—	22	nC	$V_{DS} = 50\text{ V}$
Q_{GD} Gate-to-Drain ("Miller") Charge	25	—	65	nC	See note 4
t_{ON} Turn-On Delay Time	—	—	35	ns	$V_{DD} = 50\text{ V}$, $I_D = 38\text{A}$, $R_G \approx 2.35$
t_r Rise Time	—	—	190	ns	See note 4
t_{OFF} Turn-Off Delay Time	—	—	170	ns	
t_f Fall Time	—	—	130	ns	

Source-Drain Diode Ratings and Characteristics

Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{SD} Diode Forward Voltage	—	—	1.9	V	$T_J = 25^\circ\text{C}$, $I_S = 38\text{ A}$ ³ , $V_{GS} = 0\text{ V}$
t_r Reverse Recovery Time	—	—	500	ns	$T_J = 25^\circ\text{C}$, $I_F = 38\text{A}$, $dI/dt \leq 100\text{A}/\mu\text{s}$ ³

Thermal Resistance

Parameter	Min.	Typ.	Max.	Units	Test Conditions
R_{thJC} Junction-to-Case	—	—	0.83		Mounting surface flat, smooth, and greased Typical socket mount
R_{thCS} Case-to-sink	—	0.21	—	$^\circ\text{C}/\text{W}$	
R_{thJA} Junction-to-Ambient	—	—	48		

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. @ $V_{DD} = 50\text{V}$, Starting $T_J = 25^\circ\text{C}$, $L = 100\text{ }\mu\text{H} \pm 10\%$, $R_G = 25$, Peak $I_L = 38\text{A}$
3. Pulse width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2\%$
4. See MIL-S-19500/543

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2N6768, JANTX2N6768, JANTXV2N6768
2N6770, JANTX2N6770, JANTXV2N6770

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	JANTXV, JANTX, 2N6766	Units
I_D @ $V_{GS} = 10\text{V}$, $T_C = 25^\circ\text{C}$ Continuous Drain Current	30	A
I_D @ $V_{GS} = 10\text{V}$, $T_C = 100^\circ\text{C}$ Continuous Drain Current	19	A
I_{DM} Pulsed Drain Current ¹	120	A
P_D @ $T_C = 25^\circ\text{C}$ Maximum Power Dissipation	150	W
Linear Derating Factor	1.2	W/ $^\circ\text{C}$
V_{GS} Gate-Source Voltage	± 20	V
E_{AS} Single Pulse Avalanche Energy ²	60 ⁴	mJ
I_{AR} Avalanche Current ¹	30 ⁴	A
T_J Operating Junction	-55 to 150	$^\circ\text{C}$
T_{STG} Storage Temperature Range		$^\circ\text{C}$
Lead Temperature	300(.06 from case for 10 sec)	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS} Drain-Source Breakdown Voltage	200			V	$V_{GS} = 0\text{V}$, $I_D = 1.0\text{ mA}$
$R_{DS(on)}$ Static Drain-to-Source On-State Resistance	—	—	.085		$V_{GS} = 10\text{V}$, $I_D = 19\text{ A}$ ³
	—	—	.090		$V_{GS} = 10\text{V}$, $I_D = 30\text{ A}$ ³
$V_{GS(th)}$ Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$
I_{SS} Zero Gate Voltage Drain Current	—	—	25	μA	$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$
	—	—	250		$V_{DS} = 100\text{V}$, $V_{GS} = 0\text{V}$, $T_J = 125^\circ\text{C}$
I_{SSS} Gate -to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20\text{V}$
I_{SSS} Gate -to-Source Leakage Reverse	—	—	-100	nA	$V_{GS} = -20\text{V}$
$Q_{G(on)}$ On-state Gate Charge	55	—	115	nC	$V_{GS} = 10\text{V}$, $I_D = 30\text{A}$
Q_{GS} Gate-to-Source Charge	8	—	22	nC	$V_{DS} = 100\text{V}$
Q_{Gd} Gate-to-Drain ("Miller") Charge	30	—	60	nC	See note 4
$t_{(on)}$ Turn-On Delay Time	—	—	35	ns	$V_{DD} = 100\text{V}$, $I_D = 30\text{A}$, $R_G = 2.35$ See note 4
t_r Rise Time	—	—	190	ns	
$t_{(off)}$ Turn-Off Delay Time	—	—	170	ns	
t_f Fall Time	—	—	130	ns	

Source-Drain Diode Ratings and Characteristics

Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{SD} Diode Forward Voltage	—	—	1.9	V	$T_J = 25^\circ\text{C}$, $I_S = 30\text{ A}$ ³ , $V_{GS} = 0\text{V}$
t_r Reverse Recovery Time	—	—	950	ns	$T_J = 25^\circ\text{C}$, $I_F = 30\text{ A}$, $di/dt < 100\text{A}/\mu\text{s}$ ³

Thermal Resistance

Parameter	Min.	Typ.	Max.	Units	Test Conditions
R_{thJC} Junction-to-Case	—	—	0.83	$^\circ\text{C}/\text{W}$	Mounting surface flat, smooth, and greased Typical socket mount
R_{thCS} Case-to-sink	—	0.21	—		
R_{thJA} Junction-to-Ambient	—	—	48		

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. @ $V_{DD} = 50\text{V}$, Starting $T_J = 25^\circ\text{C}$, $L = 100\text{ }\mu\text{H} \pm 10\%$, $R_G = 25$, Peak $I_L = 30\text{ A}$
3. Pulse width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2\%$
4. See MIL-S-19500/543

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2N6768, JANTX2N6768, JANTXV2N6768
2N6770, JANTX2N6770, JANTXV2N6770

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	JANTXV, JANTX, 2N6768	Units
I_D @ $V_{GS} = 10\text{V}$, $T_C = 25^\circ\text{C}$ Continuous Drain Current	14	A
I_D @ $V_{GS} = 10\text{V}$, $T_C = 100^\circ\text{C}$ Continuous Drain Current	9.0	A
I_{DM} Pulsed Drain Current ¹	56	A
P_D @ $T_C = 25^\circ\text{C}$ Maximum Power Dissipation	150	W
Linear Derating Factor	1.2	W/ $^\circ\text{C}$
V_{GS} Gate-Source Voltage	± 20	V
E_{AS} Single Pulse Avalanche Energy ²	11.3 ⁴	mJ
I_{AR} Avalanche Current ¹	14 ⁴	A
T_J Operating Junction	-55 to 150	$^\circ\text{C}$
T_{STG} Storage Temperature Range		$^\circ\text{C}$
Lead Temperature	300(.06 from case for 10 sec)	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS} Drain-Source Breakdown Voltage	400			V	$V_{GS} = 0\text{V}$, $I_D \approx 1.0\text{ mA}$
$R_{DS(on)}$ Static Drain-to-Source On-State Resistance	—	—	.300		$V_{GS} = 10\text{V}$, $I_D = 9.0\text{ A}$ ³
	—	—	.400		$V_{GS} = 10\text{V}$, $I_D = 14\text{ A}$ ³
$V_{GS(th)}$ Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$
I_{DSS} Zero Gate Voltage Drain Current	—	—	25	μA	$V_{DS} = 300\text{ V}$, $V_{GS} = 0\text{V}$
	—	—	250		$V_{DS} = 300\text{ V}$, $V_{GS} = 0\text{V}$, $T_J = 125^\circ\text{C}$
I_{SS} Gate -to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20\text{ V}$
I_{SS} Gate -to-Source Leakage Reverse	—	—	-100	nA	$V_{GS} = -20\text{ V}$
$Q_{G(on)}$ On-state Gate Charge	52	—	110	nC	$V_{GS} = 10\text{V}$, $I_D = 14\text{A}$
Q_{GS} Gate-to-Source Charge	5.0	—	18	nC	$V_{DS} = 200\text{ V}$
Q_{GD} Gate-to-Drain ("Miller") Charge	25	—	65	nC	See note 4
t_{ON} Turn-On Delay Time	—	—	35	ns	$V_{DD} = 200\text{ V}$, $I_D = 14\text{ A}$, $R_G = 2.35$ See note 4
t_r Rise Time	—	—	190	ns	
t_{OFF} Turn-Off Delay Time	—	—	170	ns	
t_f Fall Time	—	—	130	ns	

Source-Drain Diode Ratings and Characteristics

Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{SD} Diode Forward Voltage	—	—	1.7	V	$T_J = 25^\circ\text{C}$, $I_S = 14\text{ A}$ ³ , $V_{GS} = 0\text{ V}$
t_r Reverse Recovery Time	—	—	1200	ns	$T_J = 25^\circ\text{C}$, $I_F = 14\text{ A}$, $dI/dt \leq 100\text{ A}/\mu\text{s}$ ³

Thermal Resistance

Parameter	Min.	Typ.	Max.	Units	Test Conditions
R_{thJC} Junction-to-Case	—	—	0.83	$^\circ\text{C}/\text{W}$	Mounting surface flat, smooth, and greased Typical socket mount
R_{thCS} Case-to-sink	—	0.21	—		
R_{thJA} Junction-to-Ambient	—	—	48		

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. @ $V_{DD} = 50\text{ V}$, Starting $T_J = 25^\circ\text{C}$, $L = 100\text{ }\mu\text{H} \pm 10\%$, $R_G = 25$, Peak $I_L = 14\text{ A}$
3. Pulse width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2\%$
4. See MIL-S-19500/543

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2N6770, JANTX2N6770, JANTXV2N6770

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	JANTXV, JANTX, 2N6770	Units
I_D @ $V_{GS} = 10\text{V}$, $T_C = 25^\circ\text{C}$ Continuous Drain Current	12	A
I_D @ $V_{GS} = 10\text{V}$, $T_C = 100^\circ\text{C}$ Continuous Drain Current	7.75	A
I_{DM} Pulsed Drain Current ¹	48	A
P_D @ $T_C = 25^\circ\text{C}$ Maximum Power Dissipation	150	W
Linear Derating Factor	1.2	W/ $^\circ\text{C}$
V_{GS} Gate-Source Voltage	± 20	V
E_{AS} Single Pulse Avalanche Energy ²	8.0 ⁴	mJ
I_{AR} Avalanche Current ¹	12 ⁴	A
T_J Operating Junction	-55 to 150	$^\circ\text{C}$
T_{STG} Storage Temperature Range		
Lead Temperature	300(.06 from case for 10 sec)	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS @ $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS} Drain-Source Breakdown Voltage	500			V	$V_{GS} = 0\text{V}$, $I_D \leq 1.0\text{ mA}$
$R_{DS(on)}$ Static Drain-to-Source On-State Resistance	—	—	.400		$V_{GS} = 10\text{V}$, $I_D = 7.75\text{ A}$ ³
	—	—	.500		$V_{GS} = 10\text{V}$, $I_D = 12\text{ A}$ ³
$V_{GS(th)}$ Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$
I_{DSS} Zero Gate Voltage Drain Current	—	—	25	μA	$V_{DS} = 400\text{ V}$, $V_{GS} = 0\text{V}$
	—	—	250		$V_{DS} = 400\text{V}$, $V_{GS} = 0\text{V}$, $T_J = 125^\circ\text{C}$
I_{SSS} Gate -to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20\text{ V}$
I_{SSS} Gate -to-Source Leakage Reverse	—	—	-100	nA	$V_{GS} = -20\text{ V}$
$Q_{G(on)}$ On-state Gate Charge	55	—	120	nC	$V_{GS} = 10\text{V}$, $I_D = 12\text{ A}$
Q_{GS} Gate-to-Source Charge	5.0	—	19	nC	$V_{DS} = 250\text{ V}$
Q_{GD} Gate-to-Drain ("Miller") Charge	27	—	70	nC	See note 4
t_{ON} Turn-On Delay Time	—	—	35	ns	$V_{DD} = 250\text{ V}$, $I_D = 12\text{ A}$, $R_G = 2.35$
t_r Rise Time	—	—	190	ns	See note 4
t_{OFF} Turn-Off Delay Time	—	—	170	ns	
t_f Fall Time	—	—	130	ns	

Source-Drain Diode Ratings and Characteristics

Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{SD} Diode Forward Voltage	—	—	1.7	V	$T_J = 25^\circ\text{C}$, $I_S = 12\text{ A}$ ³ , $V_{GS} = 0\text{ V}$
t_r Reverse Recovery Time	—	—	1600	ns	$T_J = 25^\circ\text{C}$, $I_F = 12\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$ ³

Thermal Resistance

Parameter	Min.	Typ.	Max.	Units	Test Conditions
R_{thJC} Junction-to-Case	—	—	0.83	$^\circ\text{C}/\text{W}$	Mounting surface flat, smooth, and greased
R_{thCS} Case-to-sink	—	0.21	—		
R_{thJA} Junction-to-Ambient	—	—	48		

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. @ $V_{DD} = 50\text{ V}$, Starting $T_J = 25^\circ\text{C}$, $L = 100\text{ }\mu\text{H} \pm 10\%$, $R_G = 25$, Peak $I_L = 12\text{A}$
3. Pulse width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2\%$
4. See MIL-S-19500/543